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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	13
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 6x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.240", 6.10mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1006casp-x0

Table 1-1. List of Ordering Part Numbers

(6/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
48 pins	48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)	Mounted	A	R5F100GAANA#U0, R5F100GCANA#U0, R5F100GDANA#U0, R5F100GEANA#U0, R5F100GFANA#U0, R5F100GGANA#U0, R5F100GHANA#U0, R5F100GJANA#U0, R5F100GKANA#U0, R5F100GLANA#U0 R5F100GAANA#W0, R5F100GCANA#W0, R5F100GDANA#W0, R5F100GEANA#W0, R5F100GFANA#W0, R5F100GGANA#W0, R5F100GHANA#W0, R5F100GJANA#W0, R5F100GKANA#W0, R5F100GLANA#W0
		Not mounted	D	R5F100GADNA#U0, R5F100GCDNA#U0, R5F100GDDNA#U0, R5F100GEDNA#U0, R5F100GFDNA#U0, R5F100GGDNA#U0, R5F100GHDNA#U0, R5F100GJDNA#U0, R5F100GKDNA#U0, R5F100GLDNA#U0 R5F100GADNA#W0, R5F100GCDNA#W0, R5F100GDDNA#W0, R5F100GEDNA#W0, R5F100GFDNA#W0, R5F100GGDNA#W0, R5F100GHDNA#W0, R5F100GJDNA#W0, R5F100GKDNA#W0, R5F100GLDNA#W0
			G	R5F100GAGNA#U0, R5F100GCGNA#U0, R5F100GDGNA#U0, R5F100GEGNA#U0, R5F100GFGNA#U0, R5F100GGGNA#U0, R5F100GHGNA#U0, R5F100GJGNA#U0 R5F100GAGNA#W0, R5F100GCGNA#W0, R5F100GDGNA#W0, R5F100GEGNA#W0, R5F100GFGNA#W0, R5F100GGGNA#W0, R5F100GHGNA#W0, R5F100GJGNA#W0
		Not mounted	A	R5F101GAANA#U0, R5F101GCANA#U0, R5F101GDANA#U0, R5F101GEANA#U0, R5F101GFANA#U0, R5F101GGANA#U0, R5F101GHANA#U0, R5F101GJANA#U0, R5F101GKANA#U0, R5F101GLANA#U0 R5F101GAANA#W0, R5F101GCANA#W0, R5F101GDANA#W0, R5F101GEANA#W0, R5F101GFANA#W0, R5F101GGANA#W0, R5F101GHANA#W0, R5F101GJANA#W0, R5F101GKANA#W0, R5F101GLANA#W0
			D	R5F101GADNA#U0, R5F101GCDNA#U0, R5F101GDDNA#U0, R5F101GEDNA#U0, R5F101GFDNA#U0, R5F101GGDNA#U0, R5F101GHDNA#U0, R5F101GJDNA#U0, R5F101GKDNA#U0, R5F101GLDNA#U0 R5F101GADNA#W0, R5F101GCDNA#W0, R5F101GDDNA#W0, R5F101GEDNA#W0, R5F101GFDNA#W0, R5F101GGDNA#W0, R5F101GHDNA#W0, R5F101GJDNA#W0, R5F101GKDNA#W0, R5F101GLDNA#W0

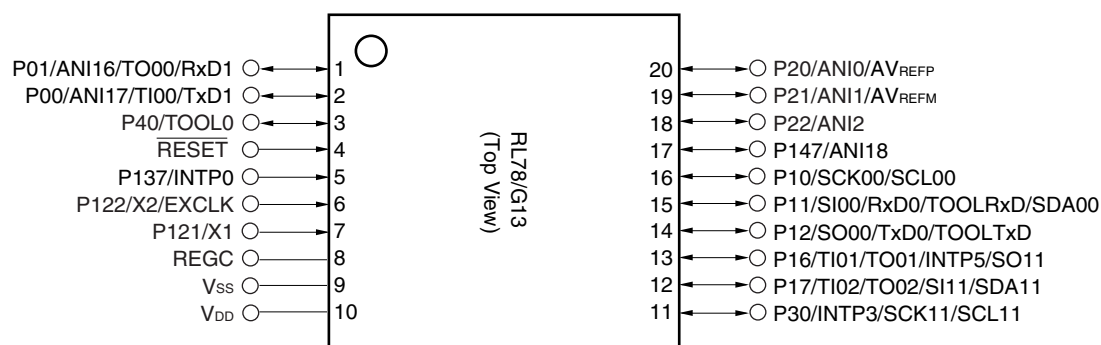
Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

1.3.1 20-pin products

- 20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)

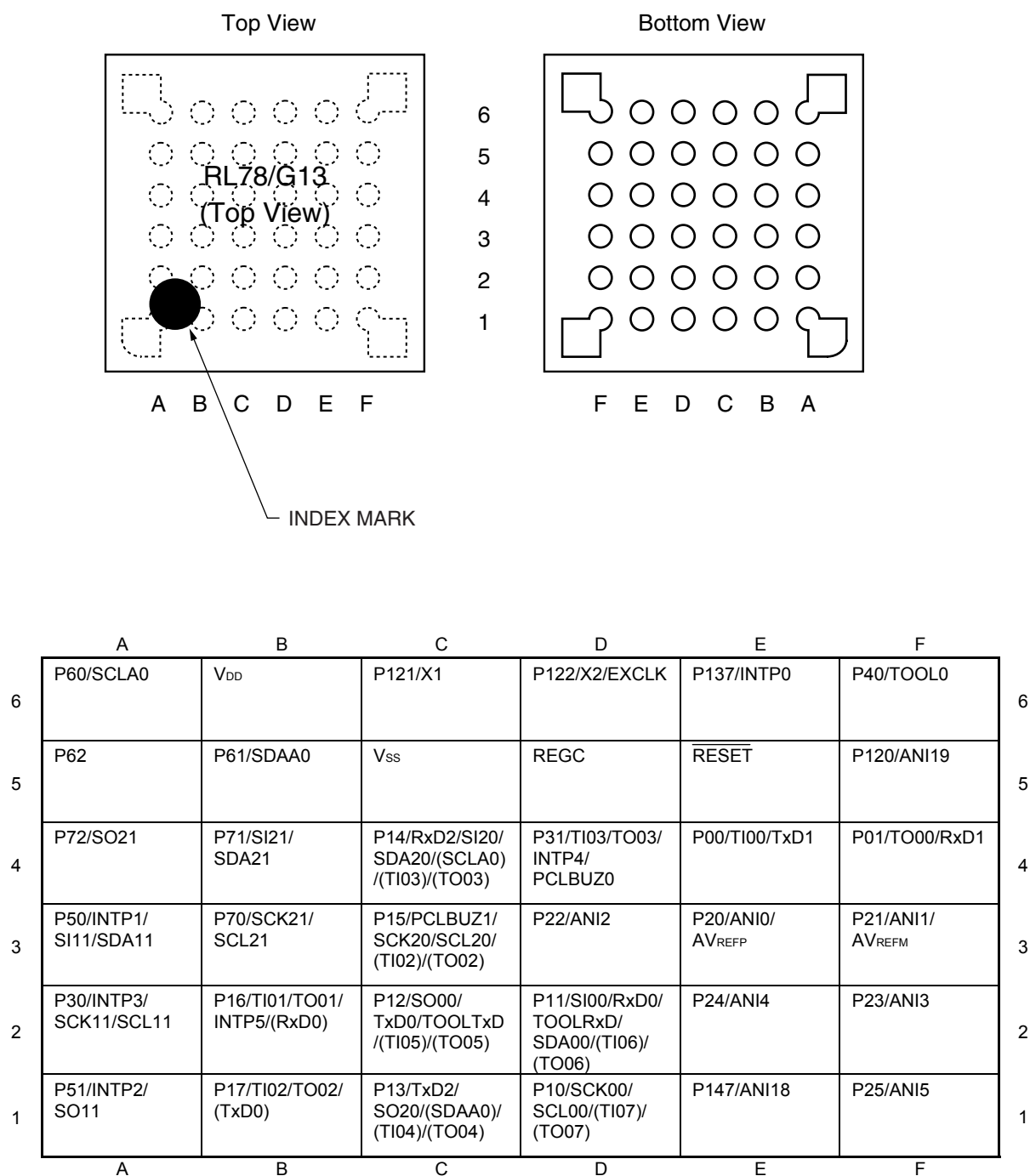


Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see 1.4 Pin Identification.

1.3.6 36-pin products

- 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)

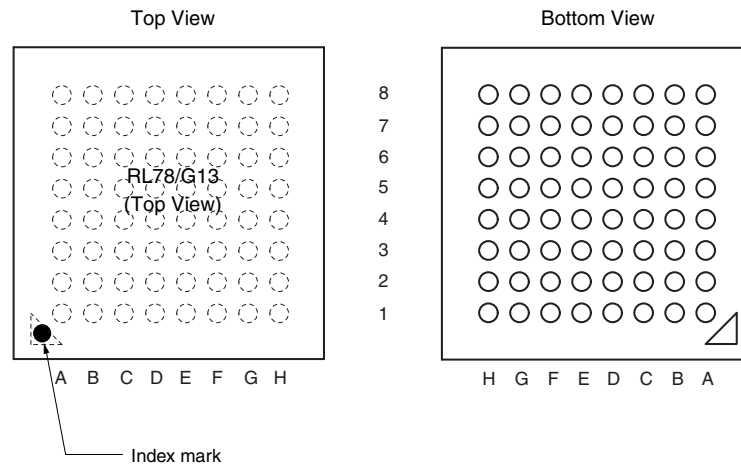


Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

- 64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)



Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A1	P05/TI05/TO05	C1	P51/INTP2/SO11	E1	P13/TxD2/SO20/(SDAA0)/(TI04)/(TO04)	G1	P146
A2	P30/INTP3/RTC1HZ/SCK11/SCL11	C2	P71/KR1/SI21/SDA21	E2	P14/RxD2/SI20/SDA20/(SCLA0)/(TI03)/(TO03)	G2	P25/ANI5
A3	P70/KR0/SCK21/SCL21	C3	P74/KR4/INTP8/SI01/SDA01	E3	P15/SCK20/SCL20/(TI02)/(TO02)	G3	P24/ANI4
A4	P75/KR5/INTP9/SCK01/SCL01	C4	P52/(INTP10)	E4	P16/TI01/TO01/INTP5/(SI00)/(RxD0)	G4	P22/ANI2
A5	P77/KR7/INTP11/(TxD2)	C5	P53/(INTP11)	E5	P03/ANI16/SI10/RxD1/SDA10	G5	P130
A6	P61/SDAA0	C6	P63	E6	P41/TI07/TO07	G6	P02/ANI17/SO10/TxD1
A7	P60/SCLA0	C7	V _{SS}	E7	RESET	G7	P00/TI00
A8	EV _{DD0}	C8	P121/X1	E8	P137/INTP0	G8	P124/XT2/EXCLKS
B1	P50/INTP1/SI11/SDA11	D1	P55/(PCLBUZ1)/(SCK00)	F1	P10/SCK00/SCL00/(TI07)/(TO07)	H1	P147/ANI18
B2	P72/KR2/SO21	D2	P06/TI06/TO06	F2	P11/SI00/RxD0/TOOLRxD/SDA00/(TI06)/(TO06)	H2	P27/ANI7
B3	P73/KR3/SO01	D3	P17/TI02/TO02/(SO00)/(TxD0)	F3	P12/SO00/TxD0/TOOLTxD/(INTP5)/(TI05)/(TO05)	H3	P26/ANI6
B4	P76/KR6/INTP10/(RxD2)	D4	P54	F4	P21/ANI1/AV _{REFM}	H4	P23/ANI3
B5	P31/TI03/TO03/INTP4/(PCLBUZ0)	D5	P42/TI04/TO04	F5	P04/SCK10/SCL10	H5	P20/ANI0/AV _{REFP}
B6	P62	D6	P40/TOOL0	F6	P43	H6	P141/PCLBUZ1/INTP7
B7	V _{DD}	D7	REGC	F7	P01/TO00	H7	P140/PCLBUZ0/INTP6
B8	EV _{SS0}	D8	P122/X2/EXCLK	F8	P123/XT1	H8	P120/ANI19

Cautions 1. Make EV_{SS0} pin the same potential as V_{SS} pin.

2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.

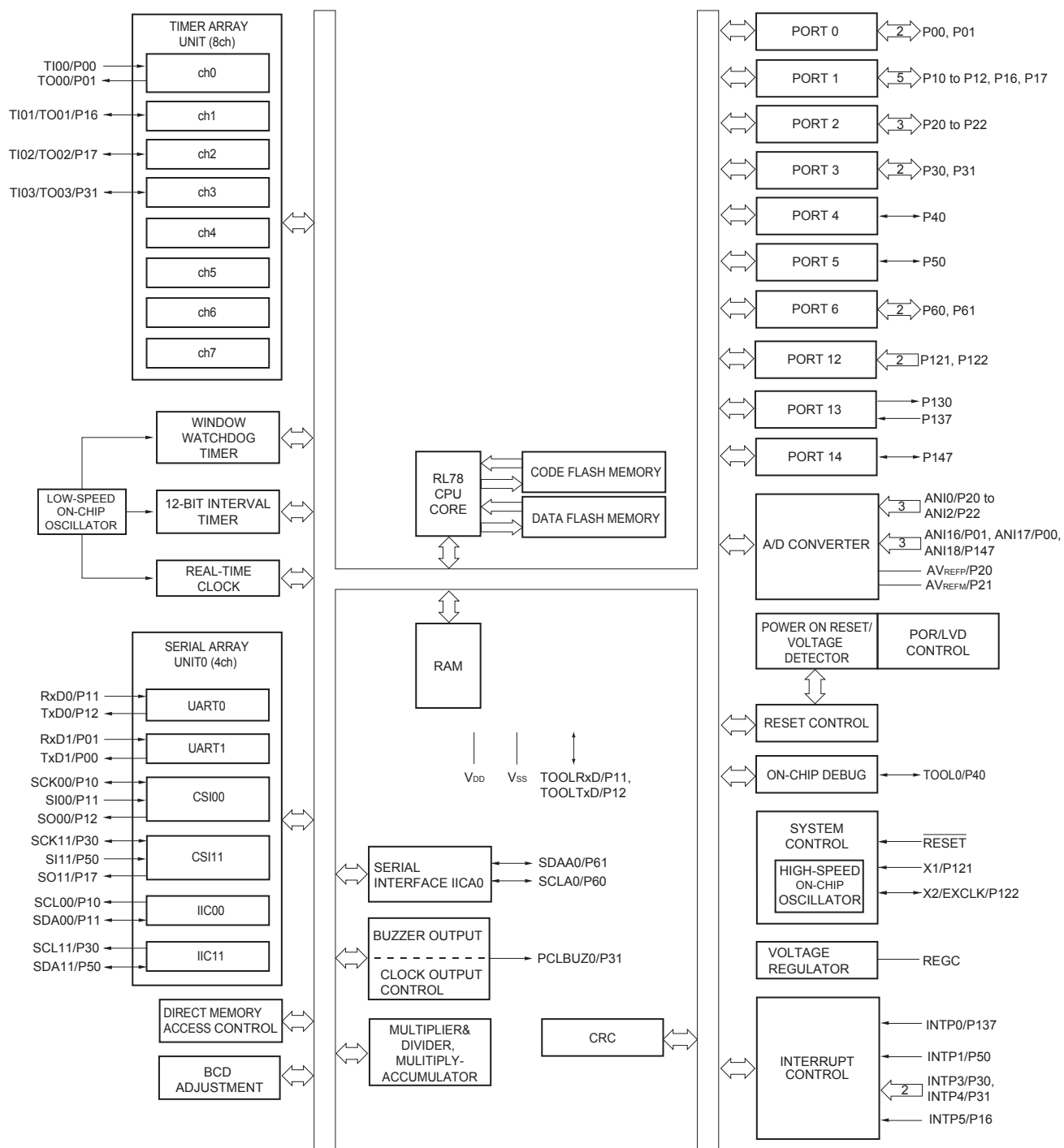
3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

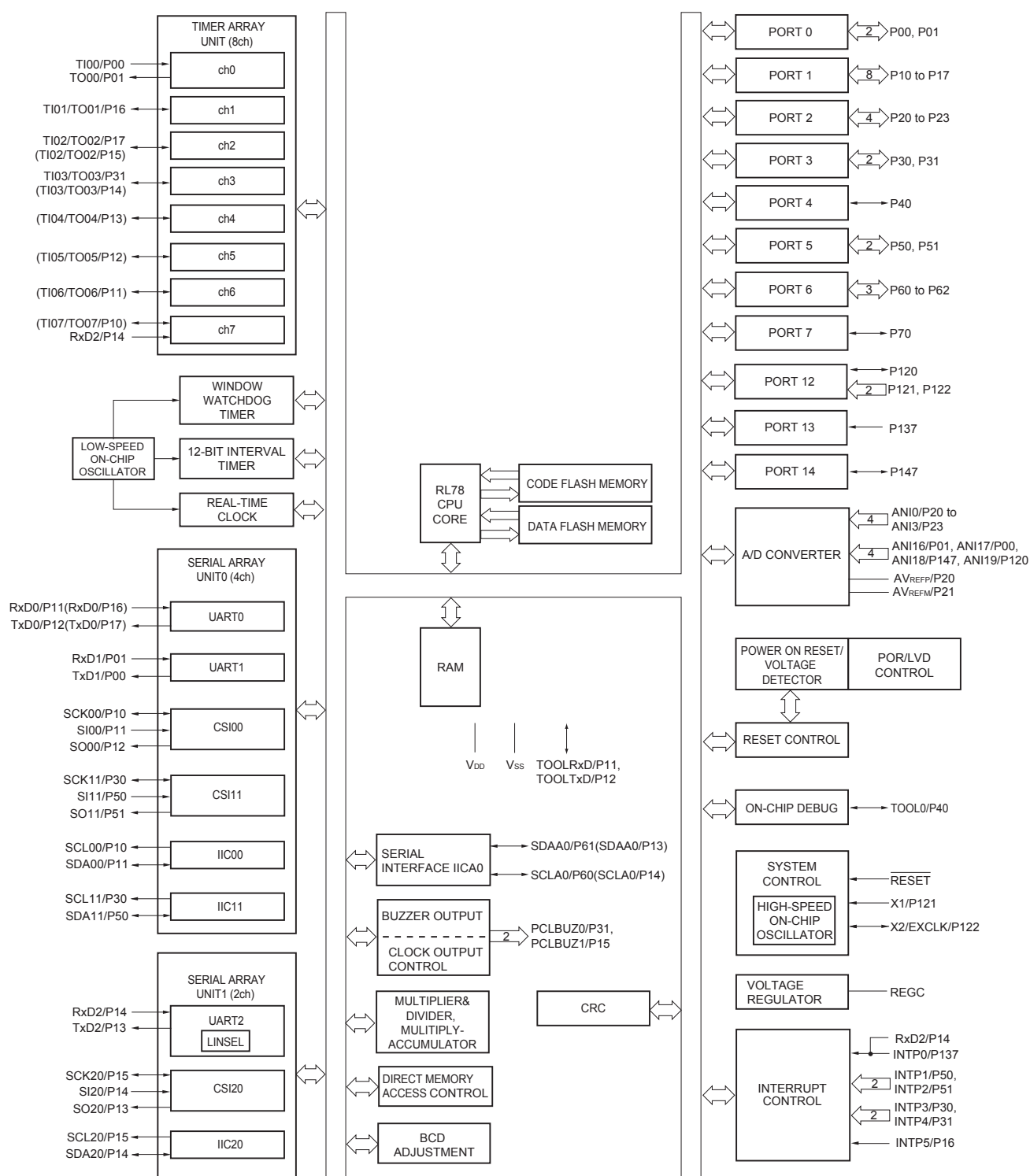
2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{SS} and EV_{SS0} pins to separate ground lines.

3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.3 25-pin products

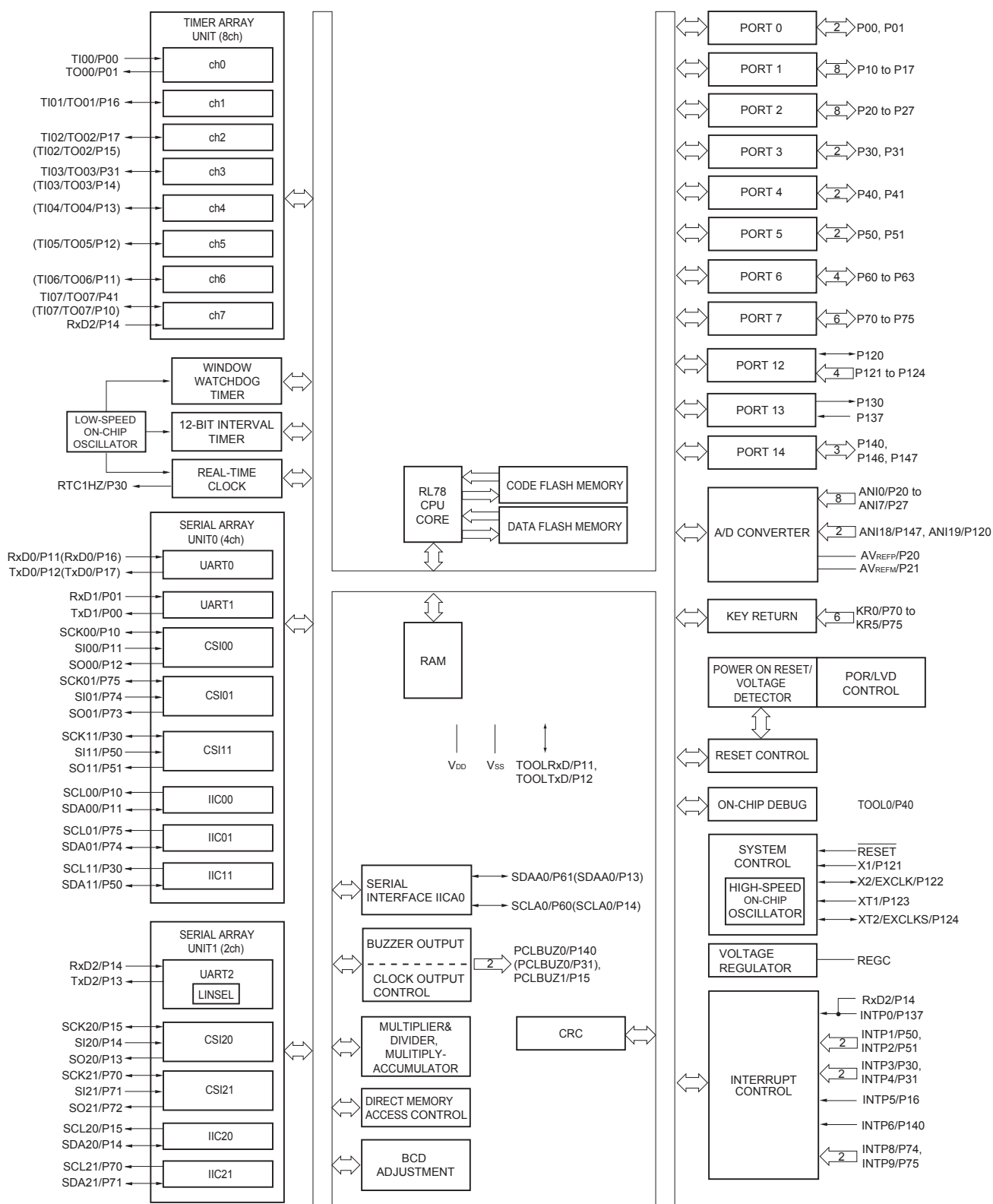


1.5.5 32-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.9 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to $+85^\circ\text{C}$)

This chapter describes the following electrical specifications.

Target products A: Consumer applications $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxAxx, R5F101xxAxx

D: Industrial applications $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxDxx, R5F101xxDxx

G: Industrial applications when $T_A = -40$ to $+105^\circ\text{C}$ products is used in the range of $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxGxx

- Cautions**
1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 2. With products not provided with an EV_{DD0} , EV_{DD1} , EV_{SS0} , or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD} , or replace EV_{SS0} and EV_{SS1} with V_{SS} .
 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

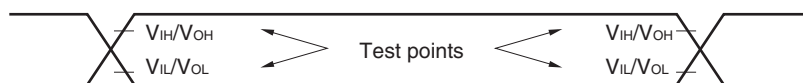
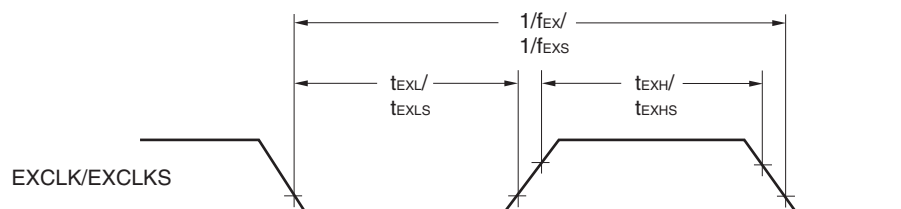
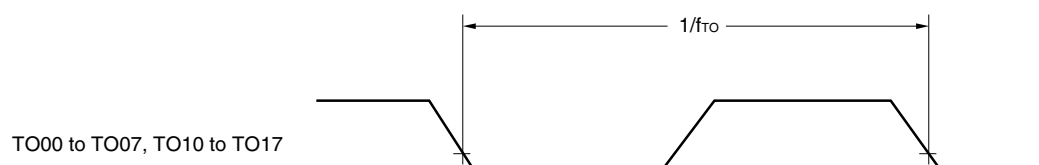
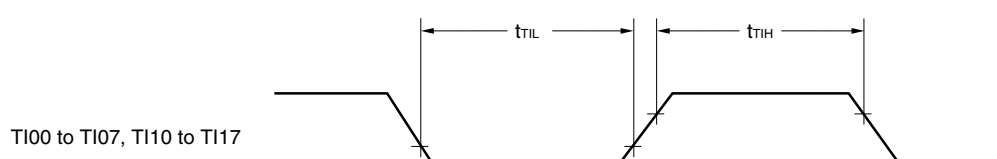
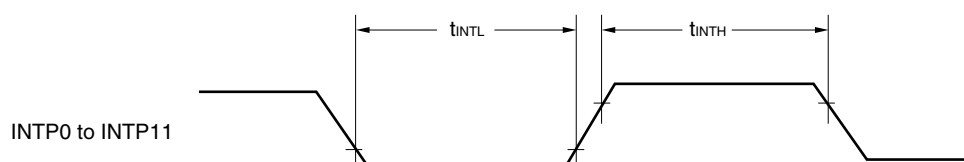
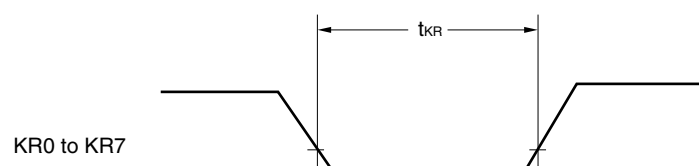
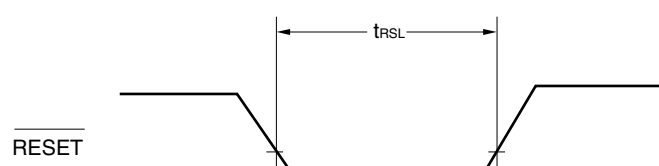
(T_A = -40 to +85°C, 1.6 V ≤ E_{VDD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = E_{VSS0} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.54	1.63	mA	
					V _{DD} = 3.0 V		0.54	1.63	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.28	mA	
					V _{DD} = 3.0 V		0.44	1.28	mA	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.40	1.00	mA	
					V _{DD} = 3.0 V		0.40	1.00	mA	
				LS (low-speed main) mode Note 7	f _{IH} = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		260	530	μA
						V _{DD} = 2.0 V		260	530	μA
				LV (low-voltage main) mode Note 7	f _{IH} = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		420	640	μA
						V _{DD} = 2.0 V		420	640	μA
			HS (high-speed main) mode Note 7	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.28	1.00	mA	
					Resonator connection		0.45	1.17	mA	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.28	1.00	mA	
					Resonator connection		0.45	1.17	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.19	0.60	mA	
					Resonator connection		0.26	0.67	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.19	0.60	mA	
					Resonator connection		0.26	0.67	mA	
			LS (low-speed main) mode Note 7	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		95	330	μA	
					Resonator connection		145	380	μA	
				f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 2.0 V	Square wave input		95	330	μA	
					Resonator connection		145	380	μA	
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5} , T _A = −40°C	Square wave input		0.25	0.57	μA	
					Resonator connection		0.44	0.76	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} , T _A = +25°C	Square wave input		0.30	0.57	μA	
					Resonator connection		0.49	0.76	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} , T _A = +50°C	Square wave input		0.37	1.17	μA	
					Resonator connection		0.56	1.36	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} , T _A = +70°C	Square wave input		0.53	1.97	μA	
					Resonator connection		0.72	2.16	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} , T _A = +85°C	Square wave input		0.82	3.37	μA	
					Resonator connection		1.01	3.56	μA	
	I _{DD3} ^{Note 6}	STOP mode ^{Note 8}	T _A = −40°C					0.18	0.50	μA
			T _A = +25°C					0.23	0.50	μA
			T _A = +50°C					0.30	1.10	μA
			T _A = +70°C					0.46	1.90	μA
			T _A = +85°C					0.75	3.30	μA

(Notes and Remarks are listed on the next page.)

6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.
7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1} , I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.
8. Current flowing only during data flash rewrite.
9. Current flowing only during self programming.
10. For shift time to the SNOOZE mode, see **18.3.3 SNOOZE mode**.

- Remarks**
1. f_{IL} : Low-speed on-chip oscillator clock frequency
 2. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 3. f_{CLK} : CPU/peripheral hardware clock frequency
 4. Temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

AC Timing Test Points**External System Clock Timing****TI/TO Timing****Interrupt Request Input Timing****Key Interrupt Input Timing****RESET Input Timing**

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (1/2)

 $(T_A = -40$ to $+85^\circ\text{C}$, $2.7\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V})$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{\text{KCY1}} \geq 2/f_{\text{CLK}}$ $4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	200		1150		1150		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	300		1150		1150		ns
SCKp high-level width	t_{KH1}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 50$		$t_{\text{KCY1}}/2 - 50$		$t_{\text{KCY1}}/2 - 50$		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 120$		$t_{\text{KCY1}}/2 - 120$		$t_{\text{KCY1}}/2 - 120$		ns
SCKp low-level width	t_{KL1}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 7$		$t_{\text{KCY1}}/2 - 50$		$t_{\text{KCY1}}/2 - 50$		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 10$		$t_{\text{KCY1}}/2 - 50$		$t_{\text{KCY1}}/2 - 50$		ns
Slp setup time (to SCKp $\uparrow$) ^{Note 1}	t_{SIK1}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	58		479		479		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	121		479		479		ns
Slp hold time (from SCKp $\uparrow$) ^{Note 1}	t_{KSI1}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	10		10		10		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	10		10		10		ns
Delay time from SCKp $\downarrow$ to SOp output ^{Note 1}	t_{KSO1}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$		60		60		60	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 20\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$		130		130		130	ns

(Notes, Caution, and Remarks are listed on the next page.)

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3		1.2	±10.5	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V _{DD} ≤ 5.5 V	57		95	μs
Conversion time	t _{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±6.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±2.5	LSB
Analog input voltage	V _{AIN}	ANI0 to ANI14	0			V _{DD}	V
		ANI16 to ANI26	0			EV _{DD0}	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{BGR} ^{Note 4}				V
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{TMPS25} ^{Note 4}				V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

2.6.5 Power supply voltage rising slope characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

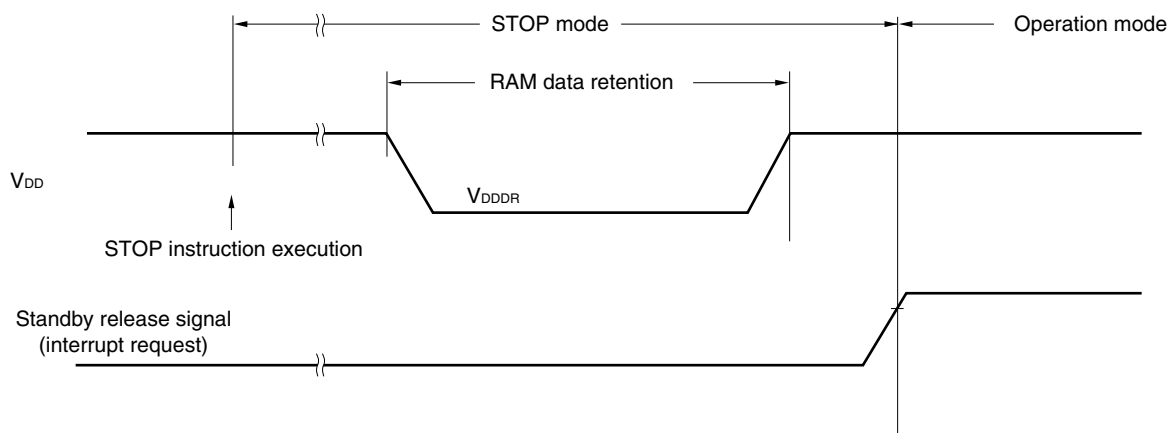
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.

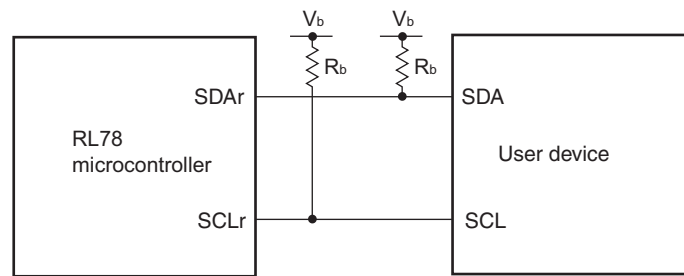
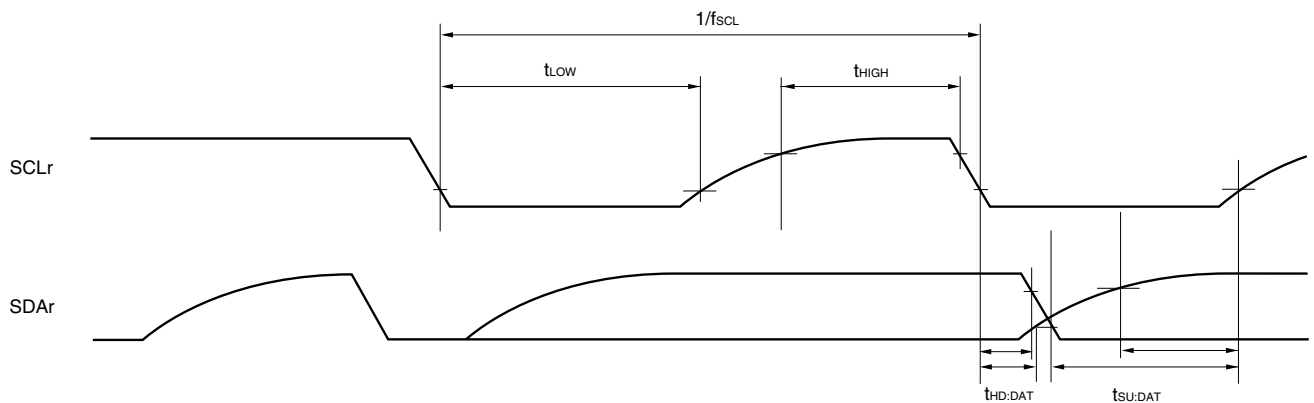


(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time ^{Note 1}	t_{KCY2}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$	$24\text{ MHz} < f_{MCK}$	$28/f_{MCK}$		ns
			$20\text{ MHz} < f_{MCK} \leq 24\text{ MHz}$	$24/f_{MCK}$		ns
			$8\text{ MHz} < f_{MCK} \leq 20\text{ MHz}$	$20/f_{MCK}$		ns
			$4\text{ MHz} < f_{MCK} \leq 8\text{ MHz}$	$16/f_{MCK}$		ns
			$f_{MCK} \leq 4\text{ MHz}$	$12/f_{MCK}$		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$	$24\text{ MHz} < f_{MCK}$	$40/f_{MCK}$		ns
			$20\text{ MHz} < f_{MCK} \leq 24\text{ MHz}$	$32/f_{MCK}$		ns
			$16\text{ MHz} < f_{MCK} \leq 20\text{ MHz}$	$28/f_{MCK}$		ns
			$8\text{ MHz} < f_{MCK} \leq 16\text{ MHz}$	$24/f_{MCK}$		ns
			$4\text{ MHz} < f_{MCK} \leq 8\text{ MHz}$	$16/f_{MCK}$		ns
			$f_{MCK} \leq 4\text{ MHz}$	$12/f_{MCK}$		ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$	$24\text{ MHz} < f_{MCK}$	$96/f_{MCK}$		ns
			$20\text{ MHz} < f_{MCK} \leq 24\text{ MHz}$	$72/f_{MCK}$		ns
			$16\text{ MHz} < f_{MCK} \leq 20\text{ MHz}$	$64/f_{MCK}$		ns
			$8\text{ MHz} < f_{MCK} \leq 16\text{ MHz}$	$52/f_{MCK}$		ns
			$4\text{ MHz} < f_{MCK} \leq 8\text{ MHz}$	$32/f_{MCK}$		ns
			$f_{MCK} \leq 4\text{ MHz}$	$20/f_{MCK}$		ns
SCKp high-/low-level width	t_{KH2} , t_{KL2}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$		$t_{KCY2}/2 - 24$		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$		$t_{KCY2}/2 - 36$		ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$ ^{Note 2}		$t_{KCY2}/2 - 100$		ns
Slp setup time (to SCKp $\uparrow$) ^{Note 2}	t_{SIK2}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$		$1/f_{MCK} + 40$		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$		$1/f_{MCK} + 40$		ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$		$1/f_{MCK} + 60$		ns
Slp hold time (from SCKp $\uparrow$) ^{Note 3}	t_{KSI2}			$1/f_{MCK} + 62$		ns
Delay time from SCKp $\downarrow$ to SOp output ^{Note 4}	t_{KSO2}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$			$2/f_{MCK} + 240$	ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$			$2/f_{MCK} + 428$	ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$			$2/f_{MCK} + 1146$	ns

(Notes, Caution and Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)**Simplified I²C mode serial transfer timing (during communication at different potential)**

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

- Remarks**
1. $R_b[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance, $V_b[V]$: Communication line voltage
 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))

3.8 Flash Memory Programming Characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f _{CLK}	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	1		32	MHz
Number of code flash rewrites Notes 1,2,3	C _{enwr}	Retained for 20 years $T_A = 85^\circ\text{C}$ Note 4	1,000			Times
Number of data flash rewrites Notes 1,2,3		Retained for 1 years $T_A = 25^\circ\text{C}$		1,000,000		
		Retained for 5 years $T_A = 85^\circ\text{C}$ Note 4	100,000			
		Retained for 20 years $T_A = 85^\circ\text{C}$ Note 4	10,000			

- Notes**
- 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 2. When using flash memory programmer and Renesas Electronics self programming library.
 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 4. This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD0} = V_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = V_{SS0} = V_{SS1} = 0\text{ V}$)

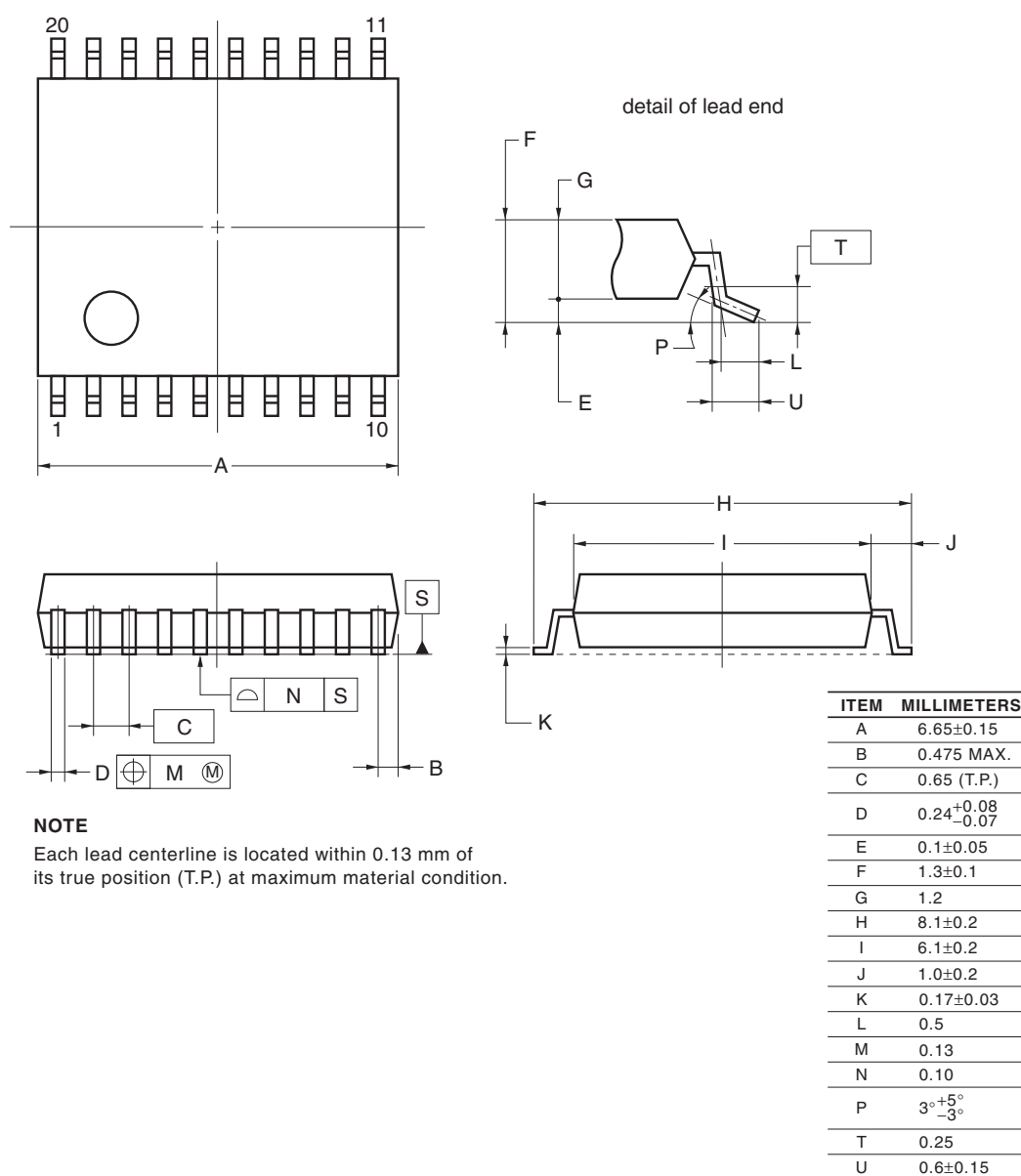
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

4. PACKAGE DRAWINGS

4.1 20-pin Products

R5F1006AASP, R5F1006CASP, R5F1006DASP, R5F1006EASP
 R5F1016AASP, R5F1016CASP, R5F1016DASP, R5F1016EASP
 R5F1006ADSP, R5F1006CDSP, R5F1006DDSP, R5F1006EDSP
 R5F1016ADSP, R5F1016CDSP, R5F1016DDSP, R5F1016EDSP
 R5F1006AGSP, R5F1006CGSP, R5F1006DGSP, R5F1006EGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-0300-0.65	PLSP0020JC-A	S20MC-65-5A4-3	0.12

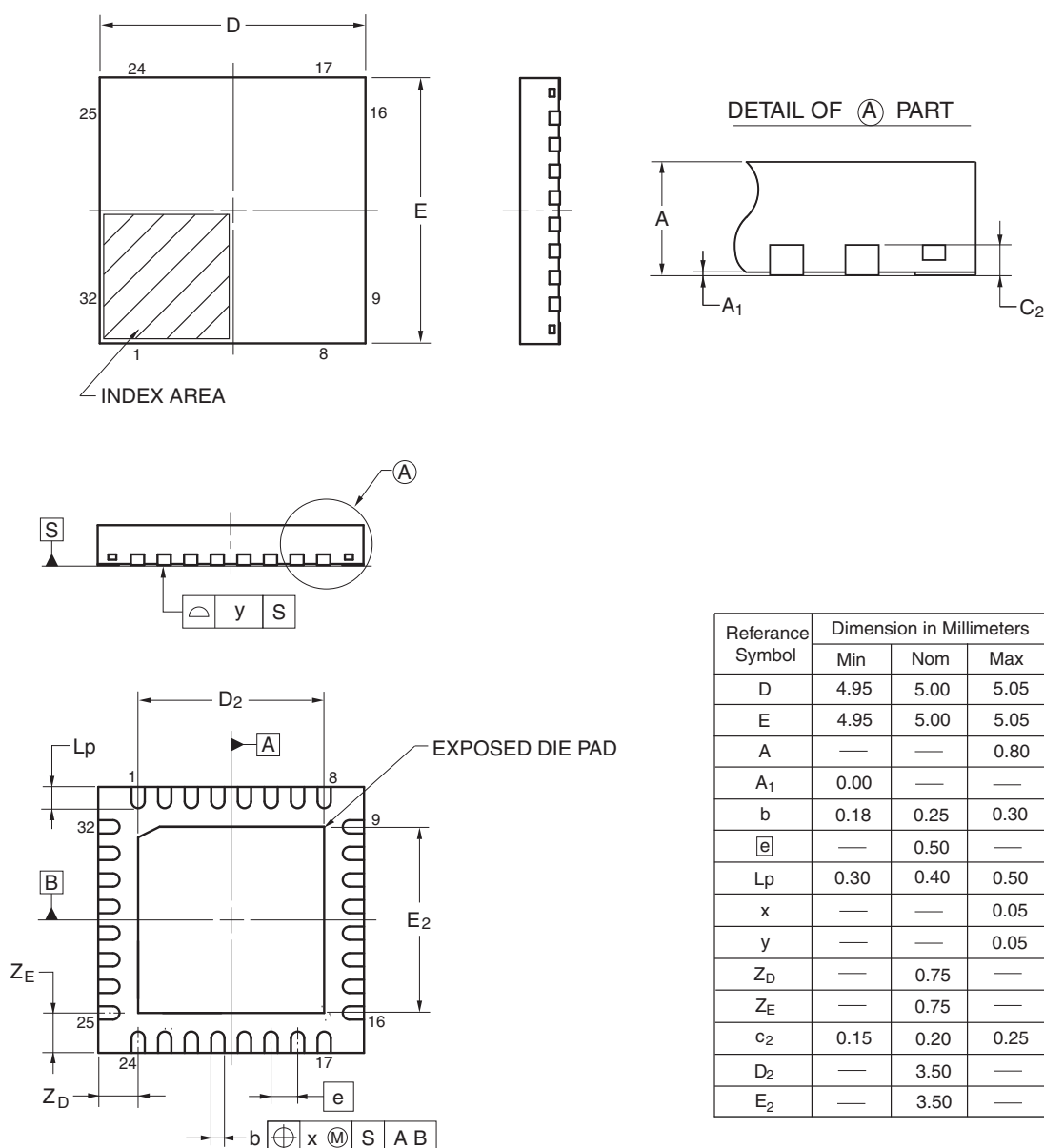


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4.5 32-pin Products

R5F100BAANA, R5F100BCANA, R5F100BDANA, R5F100BEANA, R5F100BFANA, R5F100BGANA
 R5F101BAANA, R5F101BCANA, R5F101BDANA, R5F101BEANA, R5F101BFANA, R5F101BGANA
 R5F100BADNA, R5F100BCDNA, R5F100BDDNA, R5F100BEDNA, R5F100BFDNA, R5F100BGDNA
 R5F101BADNA, R5F101BCDNA, R5F101BDDNA, R5F101BEDNA, R5F101BFDNA, R5F101BGDNA
 R5F100BAGNA, R5F100BCGNA, R5F100BDGNA, R5F100BEGNA, R5F100BFGNA, R5F100BGGNA

JEITA Package code	RENESAS code	Previous code	MASS (TYP.)[g]
P-HWQFN32-5x5-0.50	PWQN0032KB-A	P32K8-50-3B4-5	0.06



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4.9 48-pin Products

R5F100GAAFB, R5F100GCAFB, R5F100GDAFB, R5F100GEAFB, R5F100GFAFB, R5F100GGAFB,
 R5F100GHAFB, R5F100GJAFB, R5F100GKAFB, R5F100GLAFB
 R5F101GAAFB, R5F101GCAFB, R5F101GDAFB, R5F101GEAFB, R5F101GFAFB, R5F101GGAFB,
 R5F101GHAFB, R5F101GJAFB, R5F101GKAFB, R5F101GLAFB
 R5F100GADFB, R5F100GCDFB, R5F100GDDFB, R5F100GEDFB, R5F100GFDFB, R5F100GGDFB,
 R5F100GHDFB, R5F100GJDFB, R5F100GKDFB, R5F100GLDFB
 R5F101GADFB, R5F101GCDFB, R5F101GDDFB, R5F101GEDFB, R5F101GFDFB, R5F101GGDFB,
 R5F101GHDFB, R5F101GJDFB, R5F101GKDFB, R5F101GLDFB
 R5F100GAGFB, R5F100GCGFB, R5F100GDGFB, R5F100GEGFB, R5F100GFGFB, R5F100GGGFB,
 R5F100GHGFB, R5F100GJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP48-7x7-0.50	PLQP0048KF-A	P48GA-50-8EU-1	0.16

